

BDX87C BDX88C

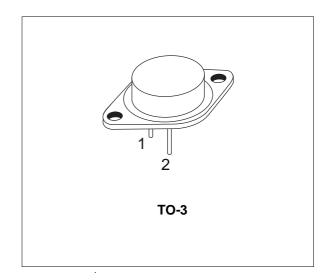
COMPLEMENTARY SILICON POWER DARLINGTON TRANSISTORS

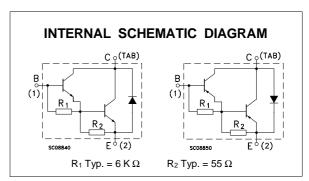
SGS-THOMSON PREFERRED SALESTYPES

DESCRIPTION

The BDX87C is a silicon epitaxial-base NPN power transistors in monolithic Darlington configuration and are mounted in Jedec TO-3 metal case. They are intented for use in power linear and switching applications.

The complementary PNP types is the BDX88C.





ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter		Value	Unit
		NPN	BDX87C	
		PNP	BDX88C	
V _{CBO}	Collector-base Voltage (I _E = 0)	100	V	
V _{CEO}	Collector-emitter Voltage (I _B = 0)		100	V
V_{EBO}	Emitter-base Voltage (I _C = 0)		5	V
Ic	Collector Current		12	Α
I _{CM}	Collector Peak Current (repetitive)		18	Α
I _B	Base Current		0.2	Α
P _{tot}	Total Dissipation at T _c ≤ 25 °C		120	W
T _{stg}	Storage Temperature		-65 to 200	°C
Tj	Max. Operating Junction Temperature		200	°C

June 1997

BDX87C-BDX88C

THERMAL DATA

R _{thj-case} Thermal Resistance Junction	se Max	1.45	°C/W
---	--------	------	------

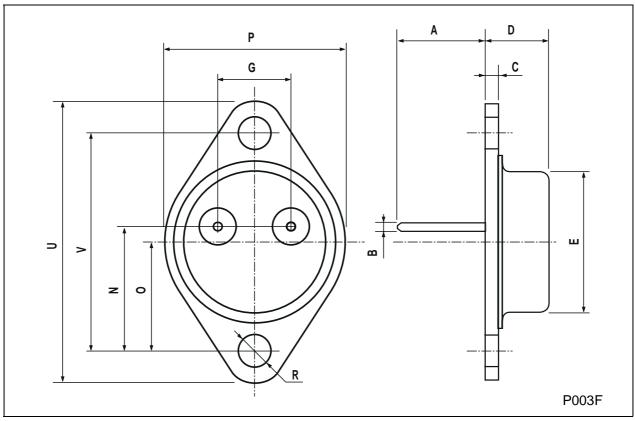
ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

Symbol	Parameter	Test (Min.	Тур.	Max.	Unit	
Ісво	Collector Cut-off Current (I _E = 0)	V _{CB} = 100 V V _{CB} = 100 V	T _{case} = 150 °C			0.5 5	mA mA
ICEO	Collector Cut-off Current (I _B = 0)	V _{CB} = 50 V				1	mA
I _{EBO}	Emitter Cut-off Current (Ic = 0)	V _{EB} = 5 V				1	mA
V _{CEO(sus)} *	Collector-Emitter Sustaining Voltage (I _B = 0)	I _C = 100 mA		100			V
V _{CE(sat)*}	Collector-emitter Saturation Voltage	I _C = 6 A I _C = 12 A	$I_B = 24 \text{ mA}$ $I_B = 120 \text{ mA}$			2 3	V V
V _{BE(sat)} *	Base-emitter Saturation Voltage	I _C = 12 A	I _B =120 mA			4	V
V _{BE} *	Base-emitter Voltage	I _C = 6 A	$V_{CE} = 3 V$			2.8	V
h _{FE} *	DC Current Gain	I _C = 5 A I _C = 6 A I _C = 12 A	V _{CE} = 3 V V _{CE} = 3 V V _{CE} = 3 V	1000 750 100		18000	
V _F *	Parallel-diode Forward Voltage	I _F = 3 A I _F = 8 A			2.5	1.8	V V
h _{fe} *	Small SignalCurrent Gain	I _C = 5 A f = 1MHz	V _{CE} = 3 V		25		

^{*} Pulsed: Pulse duration = 300 μs, duty cycle 1.5 % For PNP types voltage and current values are negative.

TO-3 MECHANICAL DATA

DIM.	mm			inch			
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
А	11.00		13.10	0.433		0.516	
В	0.97		1.15	0.038		0.045	
С	1.50		1.65	0.059		0.065	
D	8.32		8.92	0.327		0.351	
Е	19.00		20.00	0.748		0.787	
G	10.70		11.10	0.421		0.437	
N	16.50		17.20	0.649		0.677	
Р	25.00		26.00	0.984		1.023	
R	4.00		4.09	0.157		0.161	
U	38.50		39.30	1.515		1.547	
V	30.00		30.30	1.187		1.193	



BDX87C-BDX88C

Information furnished is believed to be accurate and reliable. However, SGS-THOMSON Microelectronics assumes no responsability for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may results from its use. No license is granted by implication or otherwise under any patent or patent rights of SGS-THOMSON Microelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. SGS-THOMSON Microelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of SGS-THOMSON Microelectonics.

© 1997 SGS-THOMSON Microelectronics - Printed in Italy - All Rights Reserved

SGS-THOMSON Microelectronics GROUP OF COMPANIES

Australia - Brazil - Canada - China - France - Germany - Hong Kong - Italy - Japan - Korea - Malaysia - Malta - Morocco - The Netherlands - Singapore - Spain - Sweden - Switzerland - Taiwan - Thailand - United Kingdom - U.S.A

